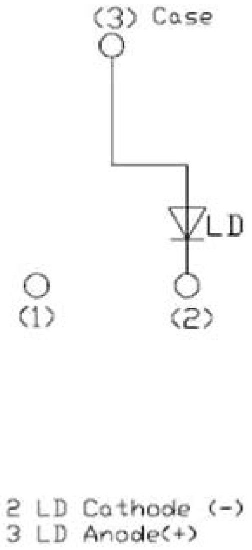
505nm Laser Diode

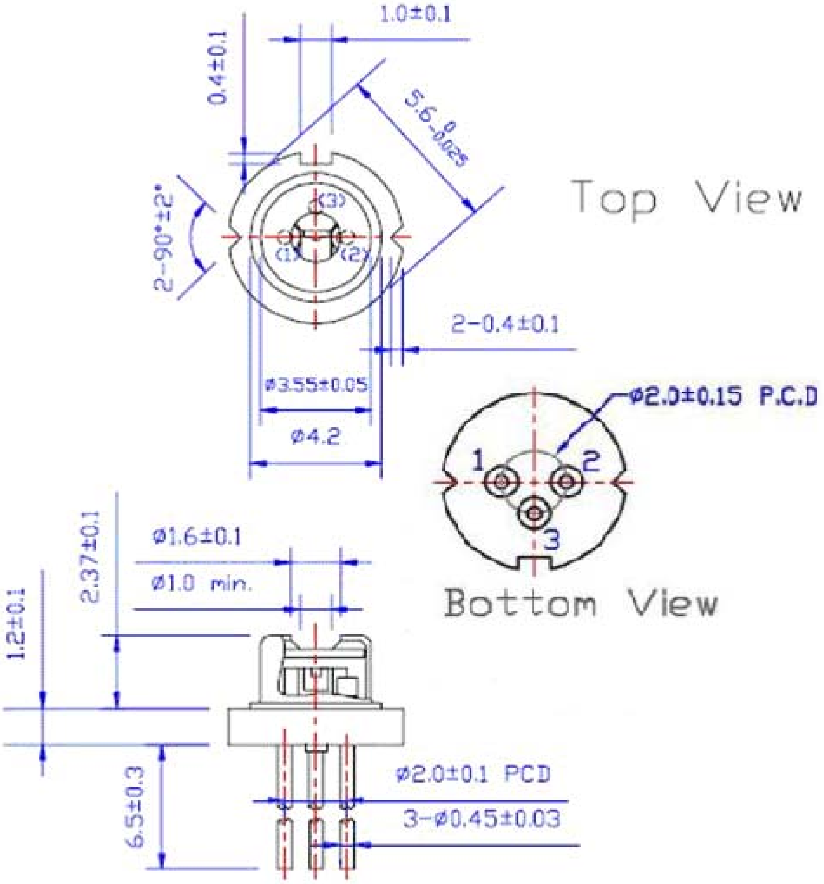
■Specifications

(1) Device: Laser Diode

(2) Structure: TO-18(ϕ 5.6mm)

■External dimensions(Unit : mm)





■Absolute Maximum Ratings(Tc=25℃)

Parameter	Ratings	Unit
Optical Output	35	mW
Operating Temperature	-10 ~ 60	℃
Storage Temperature	-40~ 85	℃
Soldering temperature	350	℃

Absolute Maximum Ratings(Tc=25℃)

Paramter	Symble	Unit	Specification			Others
			min	type	max	
Wavelength	λ	nm	495	505	515	
Output power (CW)	P_0	mW		30	35	
Threshold Current	Ith	mA		30	50	
Forward current	Iop	mA		75	100	P_0=30mW
Forward voltage	Vop	V		6.0	7.5	P_0=30mW
Sloping Efficiency	η_D	mW/mA	1.0	1.1	—	
Operating temperature	Top	℃	-10—60			
Chip Width	W	µm		120		
Cavity Length	L	µm		300		
Chip Thickness	T	µm		90		